74AUP2G38

Low-power dual 2-input NAND gate; open drain Rev. 8 — 11 February 2013 Pr

Product data sheet

General description 1.

The 74AUP2G38 provides the dual 2-input NAND gate with open-drain output. The output of the device is an open drain and can be connected to other open-drain outputs to implement active-LOW wired-OR or active-HIGH wired-AND functions.

Schmitt trigger action at all inputs makes the circuit tolerant to slower input rise and fall times across the entire V_{CC} range from 0.8 V to 3.6 V.

This device ensures a very low static and dynamic power consumption across the entire V_{CC} range from 0.8 V to 3.6 V.

This device is fully specified for partial Power-down applications using I_{OFF}. The I_{OFF} circuitry disables the output, preventing a damaging backflow current through the device when it is powered down.

2. **Features and benefits**

- Wide supply voltage range from 0.8 V to 3.6 V
- High noise immunity
- Complies with JEDEC standards:
 - ◆ JESD8-12 (0.8 V to 1.3 V)
 - ◆ JESD8-11 (0.9 V to 1.65 V)
 - ◆ JESD8-7 (1.2 V to 1.95 V)
 - ◆ JESD8-5 (1.8 V to 2.7 V)
 - ◆ JESD8-B (2.7 V to 3.6 V)
- ESD protection:
 - HBM JESD22-A114F Class 3A exceeds 5000 V
 - MM JESD22-A115-A exceeds 200 V
 - CDM JESD22-C101E exceeds 1000 V
- Low static power consumption; $I_{CC} = 0.9 \mu A$ (maximum)
- Latch-up performance exceeds 100 mA per JESD78B Class II
- Inputs accept voltages up to 3.6 V
- Low noise overshoot and undershoot < 10 % of V_{CC}
- I_{OFF} circuitry provides partial Power-down mode operation
- Multiple package options
- Specified from -40 °C to +85 °C and -40 °C to +125 °C



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3. Ordering information

Table 1. Ordering information

Type number	Package									
	Temperature range	Name	Description	Version						
74AUP2G38DC	–40 °C to +125 °C	VSSOP8	plastic very thin shrink small outline package; 8 leads; body width 2.3 mm	SOT765-1						
74AUP2G38GT	–40 °C to +125 °C	XSON8	plastic extremely thin small outline package; no leads; 8 terminals; body 1 \times 1.95 \times 0.5 mm	SOT833-1						
74AUP2G38GF	–40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body 1.35 \times 1 \times 0.5 mm	SOT1089						
74AUP2G38GD	–40 °C to +125 °C	XSON8	plastic extremely thin small outline package; no leads; 8 terminals; body 3 \times 2 \times 0.5 mm	SOT996-2						
74AUP2G38GM	–40 °C to +125 °C	XQFN8	plastic, extremely thin quad flat package; no leads; 8 terminals; body 1.6 \times 1.6 \times 0.5 mm	SOT902-2						
74AUP2G38GN	–40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body 1.2 \times 1.0 \times 0.35 mm	SOT1116						
74AUP2G38GS	–40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body $1.35 \times 1.0 \times 0.35$ mm	SOT1203						

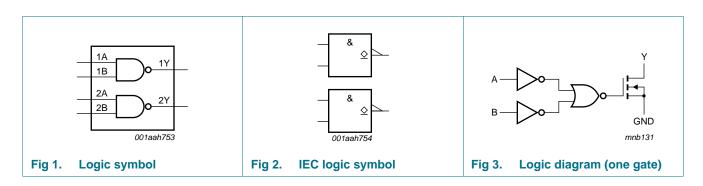
4. Marking

Table 2. Marking codes

Type number	Marking code ^[1]
74AUP2G38DC	a38
74AUP2G38GT	a38
74AUP2G38GF	аВ
74AUP2G38GD	a38
74AUP2G38GM	a38
74AUP2G38GN	аВ
74AUP2G38GS	аВ

^[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

5. Functional diagram



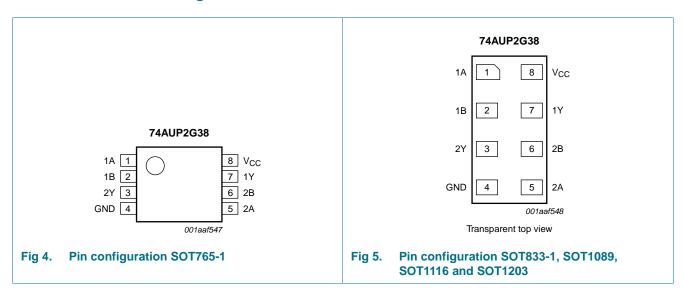
74AUP2G38

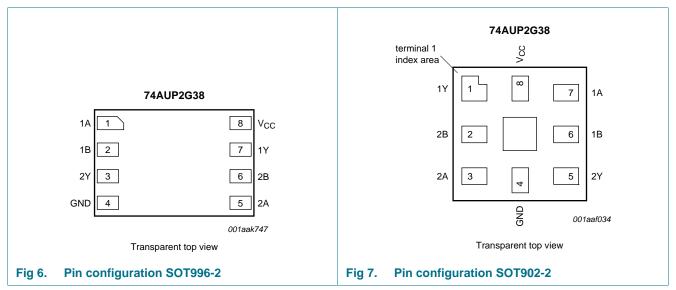
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6. Pinning information

6.1 Pinning





6.2 Pin description

Table 3. Pin description

Symbol	Pin	Pin		
	SOT765-1, SOT833-1, SOT1089, SOT996-2, SOT1116 and SOT1203	SOT902-2		
1A, 2A	1, 5	7, 3	data input	
1B, 2B	2, 6	6, 2	data input	
GND	4	4	ground (0 V)	
1Y, 2Y	7, 3	1, 5	data output	
V _{CC}	8	8	supply voltage	

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7. Functional description

Table 4. Function table[1]

Input		Output
nA	nB	nY
L	L	Z
L	Н	Z
Н	L	Z
Н	Н	L

^[1] H = HIGH voltage level;

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

		. , ,			,
Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+4.6	V
I _{IK}	input clamping current	V _I < 0 V	-50	-	mA
VI	input voltage		[<u>1</u>] -0.5	+4.6	V
I _{OK}	output clamping current	V _O < 0 V	-50	-	mA
Vo	output voltage	Active mode and Power-down mode	[<u>1</u>] -0.5	+4.6	V
I _O	output current	$V_O = 0 V \text{ to } V_{CC}$	-	+20	mA
I _{CC}	supply current		-	+50	mA
I _{GND}	ground current		-50	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	$T_{amb} = -40 ^{\circ}\text{C} \text{ to } +125 ^{\circ}\text{C}$	[2] _	250	mW

^[1] The minimum input and output voltage ratings may be exceeded if the input and output current ratings are observed.

9. Recommended operating conditions

Table 6. Operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		0.8	3.6	V
V _I	input voltage		0	3.6	V
Vo	output voltage	Active mode and Power-down mode	0	3.6	V
T _{amb}	ambient temperature		-40	+125	°C
Δt/ΔV	input transition rise and fall rate	V _{CC} = 0.8 V to 3.6 V	0	200	ns/V

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L = LOW voltage level;

Z = high-impedance OFF state.

^[2] For VSSOP8 packages: above 110 °C the value of P_{tot} derates linearly at 8.0 mW/K. For XSON8 and XQFN8 packages: above 118 °C the value of P_{tot} derates linearly with 7.8 mW/K.

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10. Static characteristics

Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$T_{amb} = 2$	5 °C					
V_{IH}	HIGH-level input voltage	$V_{CC} = 0.8 \text{ V}$	0.70V _{CC}	-	-	V
		V _{CC} = 0.9 V to 1.95 V	0.65V _{CC}	-	-	V
		V _{CC} = 2.3 V to 2.7 V	1.6	-	-	V
		V _{CC} = 3.0 V to 3.6 V	2.0	-	-	V
V_{IL}	LOW-level input voltage	V _{CC} = 0.8 V	-	-	0.30V _{CC}	V
		V _{CC} = 0.9 V to 1.95 V	-	-	0.35V _{CC}	V
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	-	-	0.7	V
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	-	-	0.9	V
V_{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		$I_O = 20 \mu A$; $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	0.1	V
		$I_O = 1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	-	-	0.3V _{CC}	V
		$I_O = 1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	-	-	0.31	V
		I _O = 1.9 mA; V _{CC} = 1.65 V	-	-	0.31	V
		$I_O = 2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.31	V
		$I_O = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.44	V
		$I_O = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.31	V
		$I_O = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.44	V
I	input leakage current	$V_I = GND$ to 3.6 V; $V_{CC} = 0$ V to 3.6 V	-	-	±0.1	μΑ
l _{OZ}	OFF-state output current	$V_I = V_{IH}$ or V_{IL} ; $V_O = 0$ V to 3.6 V; $V_{CC} = 0$ V to 3.6 V	-	-	±0.1	μА
I _{OFF}	power-off leakage current	V_I or $V_O = 0$ V to 3.6 V; $V_{CC} = 0$ V	-	-	±0.2	μΑ
ΔI_{OFF}	additional power-off leakage current	V_1 or $V_0 = 0$ V to 3.6 V; $V_{CC} = 0$ V to 0.2 V	-	-	±0.2	μА
I _{CC}	supply current	$V_I = GND \text{ or } V_{CC}; I_O = 0 \text{ A};$ $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	0.5	μА
ΔI_{CC}	additional supply current	$V_I = V_{CC} - 0.6 \text{ V}; I_O = 0 \text{ A};$ $V_{CC} = 3.3 \text{ V}$	-	-	40	μА
C _I	input capacitance	V_{CC} = 0 V to 3.6 V; V_I = GND or V_{CC}	-	0.7	-	pF
Co	output capacitance	$V_O = GND; V_{CC} = 0 V$	-	0.9	-	pF

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Unit

Table 7. Static characteristics ...continued
At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

V_{IH}	HIGH-level input voltage	$V_{CC} = 0.8 \text{ V}$	0.70V _{CC}	-	-	V
	. •	V _{CC} = 0.9 V to 1.95 V	0.65V _{CC}	-	-	V
		V _{CC} = 2.3 V to 2.7 V	1.6	-	-	V
		V _{CC} = 3.0 V to 3.6 V	2.0	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 0.8 V	-	-	0.30V _{CC}	V
		$V_{CC} = 0.9 \text{ V to } 1.95 \text{ V}$	-	-	0.35V _{CC}	V
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	-	-	0.7	V
		V _{CC} = 3.0 V to 3.6 V	-	-	0.9	V
V _{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		$I_O = 20 \mu A$; $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	0.1	V
		I _O = 1.1 mA; V _{CC} = 1.1 V	-	-	0.3V _{CC}	V
		$I_O = 1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	-	-	0.37	V
		$I_O = 1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	-	-	0.35	V
		$I_{O} = 2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.33	V
		$I_O = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.45	V
		$I_{O} = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.33	V
		$I_O = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.45	V
l _l	input leakage current	$V_I = GND$ to 3.6 V; $V_{CC} = 0$ V to 3.6 V	-	-	±0.5	μΑ
l _{OZ}	OFF-state output current	$V_I = V_{IH}$ or V_{IL} ; $V_O = 0$ V to 3.6 V; $V_{CC} = 0$ V to 3.6 V	-	-	±0.5	μΑ
I _{OFF}	power-off leakage current	V_I or $V_O = 0$ V to 3.6 V; $V_{CC} = 0$ V	-	-	±0.5	μΑ
ΔI_{OFF}	additional power-off leakage current	V_1 or $V_0 = 0$ V to 3.6 V; $V_{CC} = 0$ V to 0.2 V	-	-	±0.6	μΑ
CC	supply current	V_I = GND or V_{CC} ; I_O = 0 A; V_{CC} = 0.8 V to 3.6 V	-	-	0.9	μΑ
Δl _{CC}	additional supply current	$V_I = V_{CC} - 0.6 \text{ V}; I_O = 0 \text{ A};$ $V_{CC} = 3.3 \text{ V}$	-	-	50	μΑ

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Table 7. Static characteristics ...continued
At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Parameter	Conditions	Min	Тур	Max	Unit
40 °C to +125 °C					
HIGH-level input voltage	$V_{CC} = 0.8 \text{ V}$	0.75V _{CC}	-	-	V
	V _{CC} = 0.9 V to 1.95 V	0.70V _{CC}	-	-	V
	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	1.6	-	-	V
	V _{CC} = 3.0 V to 3.6 V	2.0	-	-	V
LOW-level input voltage	V _{CC} = 0.8 V	-	-	0.25V _{CC}	V
	V _{CC} = 0.9 V to 1.95 V	-	-	0.30V _{CC}	V
	V _{CC} = 2.3 V to 2.7 V	-	-	0.7	V
	V _{CC} = 3.0 V to 3.6 V	-	-	0.9	V
LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}				
	$I_O = 20 \mu A$; $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	0.11	V
	I _O = 1.1 mA; V _{CC} = 1.1 V	-	-	0.33V _{CC}	V
	I _O = 1.7 mA; V _{CC} = 1.4 V	-	-	0.41	V
	$I_O = 1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	-	-	0.39	V
	$I_O = 2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.36	V
	$I_O = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.50	V
	$I_O = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.36	V
	$I_O = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.50	V
input leakage current	$V_I = GND$ to 3.6 V; $V_{CC} = 0$ V to 3.6 V	-	-	±0.75	μΑ
OFF-state output current	$V_I = V_{IH}$ or V_{IL} ; $V_O = 0$ V to 3.6 V; $V_{CC} = 0$ V to 3.6 V	-	-	±0.75	μΑ
power-off leakage current	V_I or $V_O = 0$ V to 3.6 V; $V_{CC} = 0$ V	-	-	±0.75	μΑ
additional power-off leakage current	V_1 or $V_0 = 0$ V to 3.6 V; $V_{CC} = 0$ V to 0.2 V	-	-	±0.75	μΑ
supply current	$V_I = GND \text{ or } V_{CC}; I_O = 0 \text{ A};$ $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	1.4	μΑ
additional supply current	$V_I = V_{CC} - 0.6 \text{ V}; I_O = 0 \text{ A};$ $V_{CC} = 3.3 \text{ V}$	-	-	75	μΑ
	LOW-level input voltage LOW-level output voltage input leakage current OFF-state output current power-off leakage current additional power-off leakage current supply current	$\label{eq:highest_objective} \begin{array}{ll} \text{HIGH-level input voltage} & V_{\text{CC}} = 0.8 \text{ V} \\ V_{\text{CC}} = 0.9 \text{ V to } 1.95 \text{ V} \\ V_{\text{CC}} = 2.3 \text{ V to } 2.7 \text{ V} \\ V_{\text{CC}} = 3.0 \text{ V to } 3.6 \text{ V} \\ \hline \\ \text{LOW-level input voltage} & V_{\text{CC}} = 0.8 \text{ V} \\ V_{\text{CC}} = 0.9 \text{ V to } 1.95 \text{ V} \\ V_{\text{CC}} = 2.3 \text{ V to } 2.7 \text{ V} \\ \hline \\ V_{\text{CC}} = 3.0 \text{ V to } 3.6 \text{ V} \\ \hline \\ \text{LOW-level output voltage} & V_{\text{I}} = V_{\text{IH}} \text{ or } V_{\text{IL}} \\ \hline \\ I_{\text{O}} = 20 \mu\text{A; } V_{\text{CC}} = 0.8 \text{ V to } 3.6 \text{ V} \\ \hline \\ I_{\text{O}} = 1.1 \text{ mA; } V_{\text{CC}} = 1.1 \text{ V} \\ \hline \\ I_{\text{O}} = 1.7 \text{ mA; } V_{\text{CC}} = 1.4 \text{ V} \\ \hline \\ I_{\text{O}} = 1.9 \text{ mA; } V_{\text{CC}} = 1.65 \text{ V} \\ \hline \\ I_{\text{O}} = 2.3 \text{ mA; } V_{\text{CC}} = 2.3 \text{ V} \\ \hline \\ I_{\text{O}} = 2.7 \text{ mA; } V_{\text{CC}} = 2.3 \text{ V} \\ \hline \\ I_{\text{O}} = 2.7 \text{ mA; } V_{\text{CC}} = 3.0 \text{ V} \\ \hline \\ I_{\text{O}} = 4.0 \text{ mA; } V_{\text{CC}} = 3.0 \text{ V} \\ \hline \\ I_{\text{O}} = 4.0 \text{ mA; } V_{\text{CC}} = 3.0 \text{ V} \\ \hline \\ \text{Input leakage current} & V_{\text{I}} = \text{GND to } 3.6 \text{ V; } V_{\text{CC}} = 0 \text{ V to } 3.6 \text{ V; } \\ \hline \\ \text{VCC} = 0 \text{ V to } 3.6 \text{ V; } \\ \hline \\ \text{VCC} = 0 \text{ V to } 3.6 \text{ V; } \\ \hline \\ \text{VCC} = 0 \text{ V to } 3.6 \text{ V; } \\ \hline \\ \text{Supply current} & V_{\text{I}} = \text{GND or } V_{\text{CC}}; I_{\text{O}} = 0 \text{ A; } \\ \hline \\ \text{VCC} = 0.8 \text{ V to } 3.6 \text{ V; } \\ \hline \\ \text{Additional supply current} & V_{\text{I}} = \text{V}_{\text{CC}} - 0.6 \text{ V; } I_{\text{O}} = 0 \text{ A; } \\ \hline \\ \text{VCC} = 0.8 \text{ V to } 3.6 \text{ V; } \\ \hline \\ \text{VCC} = 0.8 \text{ V to } 3.6 \text{ V; } \\ \hline \\ \text{VI} = \text{GND or } V_{\text{CC}}; I_{\text{O}} = 0 \text{ A; } \\ \hline \\ \text{VCC} = 0.8 \text{ V to } 3.6 \text{ V; } \\ \hline \\ \text{VCC} = 0.8 \text{ V to } 3.6 \text{ V; } \\ \hline \\ \text{VCC} = 0.8 \text{ V to } 3.6 \text{ V; } \\ \hline \\ \text{VCC} = 0.8 \text{ V to } 3.6 \text{ V; } \\ \hline \\ \text{VCC} = 0.8 \text{ V to } 3.6 \text{ V; } \\ \hline \\ \text{VCC} = 0.8 \text{ V to } 3.6 \text{ V; } \\ \hline \\ \text{VCC} = 0.8 \text{ V to } 3.6 \text{ V; } \\ \hline \\ \text{VCC} = 0.8 \text{ V to } 3.6 \text{ V; } \\ \hline \\ \text{VCC} = 0.8 \text{ V to } 3.6 \text{ V; } \\ \hline \\ \text{VCC} = 0.8 \text{ V to } 3.6 \text{ V; } \\ \hline \\ \text{VCC} = 0.8 \text{ V to } 3.6 \text{ V; } \\ \hline \\ \text{VCC} = 0.8 \text{ V to } 3.6 \text{ V; } \\ \hline \\ \text{VCC} = 0.8 \text{ V to } 3.6 V$	$\label{eq:high-level input voltage} \begin{tabular}{ll} $V_{CC} = 0.8 \ V$ & 0.75V_{CC}$ \\ \hline $V_{CC} = 0.9 \ V$ to 1.95 \ V$ & 0.70V_{CC}$ \\ \hline $V_{CC} = 2.3 \ V$ to 2.7 \ V$ & 1.6$ \\ \hline $V_{CC} = 3.0 \ V$ to 3.6 \ V$ & 2.0$ \\ \hline $V_{CC} = 0.8 \ V$ & -$ \\ \hline $V_{CC} = 0.9 \ V$ to 1.95 \ V$ & -$ \\ \hline $V_{CC} = 0.9 \ V$ to 1.95 \ V$ & -$ \\ \hline $V_{CC} = 2.3 \ V$ to 2.7 \ V$ & -$ \\ \hline $V_{CC} = 2.3 \ V$ to 3.6 \ V$ & -$ \\ \hline $V_{CC} = 3.0 \ V$ to 3.6 \ V$ & -$ \\ \hline $V_{CC} = 3.0 \ V$ to 3.6 \ V$ & -$ \\ \hline $I_{O} = 20 \ \mu A; \ V_{CC} = 0.8 \ V$ to 3.6 \ V$ & -$ \\ \hline $I_{O} = 1.1 \ mA; \ V_{CC} = 1.1 \ V$ & -$ \\ \hline $I_{O} = 1.7 \ mA; \ V_{CC} = 1.4 \ V$ & -$ \\ \hline $I_{O} = 1.9 \ mA; \ V_{CC} = 1.4 \ V$ & -$ \\ \hline $I_{O} = 2.3 \ mA; \ V_{CC} = 2.3 \ V$ & -$ \\ \hline $I_{O} = 2.3 \ mA; \ V_{CC} = 2.3 \ V$ & -$ \\ \hline $I_{O} = 2.7 \ mA; \ V_{CC} = 2.3 \ V$ & -$ \\ \hline $I_{O} = 2.7 \ mA; \ V_{CC} = 3.0 \ V$ & -$ \\ \hline $I_{O} = 2.7 \ mA; \ V_{CC} = 3.0 \ V$ & -$ \\ \hline $I_{O} = 4.0 \ mA; \ V_{CC} = 3.0 \ V$ & -$ \\ \hline $I_{O} = 4.0 \ mA; \ V_{CC} = 0 \ V$ to 3.6 \ V$ & -$ \\ \hline OFF-state output current & V_{I} = OND \ to 3.6 \ V; \ V_{CC} = 0 \ V$ to 3.6 \ V$ & -$ \\ \hline $additional \ power-off \ leakage \ current & V_{I} \ or \ V_{O} = 0 \ V$ to 3.6 \ V; \ V_{CC} = 0 \ V$ to 3.6 \ V$ & -$ \\ \hline $additional \ power-off \ leakage \ current & V_{I} = OND \ or \ V_{CC}; \ I_{O} = 0 \ A; \ V_{CC} = 0 \ V$ to 3.6 \ V$ \\ \hline $additional \ supply \ current & V_{I} = V_{CC} - 0.6 \ V; \ I_{O} = 0 \ A; \ V_{CC} = 0 \ A; \ V_{CC} = 0.8 \ V$ to 3.6 \ V$ \\ \hline $additional \ supply \ current & V_{I} = V_{CC} - 0.6 \ V; \ I_{O} = 0 \ A; \ V_{CC} = 0 \ A; \ V_{CC} = 0.0 \ A; \ V_{CC} =$	$\begin{tabular}{l l l l l l l l l l l l l l l l l l l $	$\label{eq:high-level input voltage} \begin{tabular}{l l l l l l l l l l l l l l l l l l l $

Low-power dual 2-input NAND gate; open drain

11. Dynamic characteristics

Table 8. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 9.

Symbol	Parameter	Conditions		25 °C		-4	0 °C to +1	25 °C	Unit
			Min	Typ[1]	Max	Min	Max (85 °C)	Max (125 °C)	
$C_L = 5 pF$			'	'	'	•		'	'
t_{pd}	propagation delay	nA, nB to nY; see Figure 8	2]						
	, , ,	$V_{CC} = 0.8 \text{ V}$	-	13.5	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$	1.9	4.6	10.4	1.8	11.4	12.6	ns
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$	1.5	3.3	6.5	1.4	7.4	8.2	ns
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$	1.2	2.9	5.1	1.1	5.9	6.5	ns
		V_{CC} = 2.3 V to 2.7 V	1.0	2.2	3.8	0.9	4.5	4.9	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	0.9	2.3	4.0	8.0	4.5	4.9	ns
$C_L = 10 p$	F								
t _{pd}	propagation delay	nA, nB to nY; see Figure 8	2]						
		$V_{CC} = 0.8 \text{ V}$	-	16.3	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$	2.3	5.6	12.3	2.1	13.7	15.1	ns
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$	1.8	3 4.1	7.6	1.7	8.8	9.7	ns
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$	1.6	3.8	6.1	1.4	7.1	7.8	ns
		V_{CC} = 2.3 V to 2.7 V	1.4	2.9	4.6	1.2	5.4	5.9	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	1.3	3.2	5.7	1.1	6.4	7.0	ns
$C_{L} = 15 p$	F								
t_{pd}	propagation delay	nA, nB to nY; see Figure 8	<u>2]</u>						
		$V_{CC} = 0.8 \text{ V}$	-	19.0	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$	2.6	6.6	14.2	2.4	15.8	17.4	ns
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$	2.1	4.8	8.7	1.9	10.1	11.1	ns
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$	1.9	4.6	7.6	1.7	8.5	9.3	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	1.6	3.6	5.6	1.5	6.3	6.9	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	1.6	4.1	7.5	1.4	8.3	9.1	ns
$C_L = 30 p$	F								
t_{pd}	propagation delay	nA, nB to nY; see Figure 8	<u>2]</u>						
		$V_{CC} = 0.8 \text{ V}$	-	27.0	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$	3.6	9.5	19.5	3.2	21.8	24.0	ns
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$	2.9	7.0	11.5	2.6	13.6	15.0	ns
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$	2.6	7.0	12.1	2.3	13.3	14.6	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	2.4	5.4	8.9	2.1	9.9	10.9	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	2.3	6.5	12.7	2.1	13.9	15.3	ns

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 Table 8.
 Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 9.

Symbol	Parameter	Conditions		25 °C		-40	0 °C to +1	25 °C	Unit	
				Min	Typ[1]	Max	Min	Max (85 °C)	Max (125 °C)	
$C_L = 5 pF$	10 pF, 15 pF and 3	0 pF								
C _{PD} power dissipation	$f = 1 \text{ MHz}; V_I = \text{GND to } V_{CC}$	[3]								
	capacitance	$V_{CC} = 0.8 \text{ V}$		-	0.6	-	-	-	-	pF
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$		-	0.7	-	-	-	-	pF
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$		-	0.8	-	-	-	-	pF
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		-	0.9	-	-	-	-	pF
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		-	1.1	-	-	-	-	pF
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		-	1.4	-	-	-	-	pF

^[1] All typical values are measured at nominal V_{CC}.

 $P_D = C_{PD} \times V_{CC}{}^2 \times f_i \times N$ where:

 f_i = input frequency in MHz;

V_{CC} = supply voltage in V;

N = number of inputs switching.

12. Waveforms

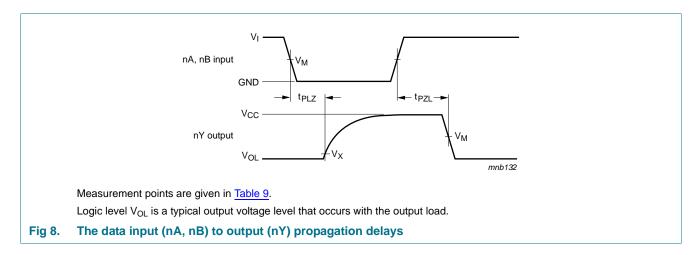


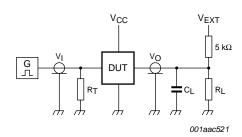
Table 9. Measurement points

Supply voltage	Input	Output				
V _{CC}	V _M	V _M	V _X			
0.8 V to 1.6 V	0.5V _{CC}	0.5V _{CC}	V _{OL} + 0.1 V			
1.65 V to 2.7 V	0.5V _{CC}	0.5V _{CC}	V _{OL} + 0.15 V			
3.0 V to 3.6 V	0.5V _{CC}	0.5V _{CC}	V _{OL} + 0.3 V			

^[2] t_{pd} is the same as t_{PZL} and t_{PLZ} .

^[3] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

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Test data is given in Table 10.

Definitions for test circuit:

R_L = Load resistance.

C_L = Load capacitance including jig and probe capacitance.

 R_T = Termination resistance should be equal to the output impedance Z_o of the pulse generator.

 V_{EXT} = External voltage for measuring switching times.

Fig 9. Test circuit for measuring switching times

Table 10. Test data

Supply voltage	Load		V _{EXT}				
V _{CC}	CL	R _L [1]	t _{PLH} , t _{PHL}	t _{PZH} , t _{PHZ}	t _{PZL} , t _{PLZ}		
0.8 V to 3.6 V	5 pF, 10 pF, 15 pF and 30 pF	5 k Ω or 1 M Ω	open	GND	2V _{CC}		

[1] For measuring enable and disable times R_L = 5 k Ω .

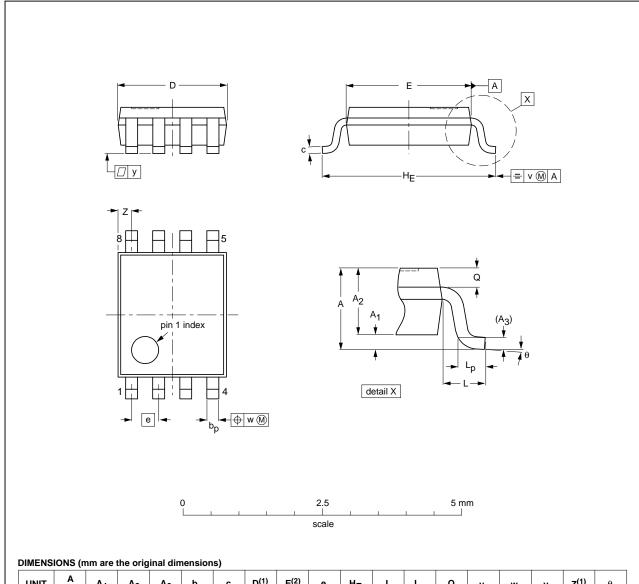
For measuring propagation delays, set-up times, hold times and pulse width, R_L = 1 $M\Omega$.

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13. Package outline

VSSOP8: plastic very thin shrink small outline package; 8 leads; body width 2.3 mm

SOT765-1



UNIT	A max.	A ₁	A ₂	А3	bp	С	D ⁽¹⁾	E ⁽²⁾	е	HE	L	Lp	Q	v	w	у	Z ⁽¹⁾	θ
mm	1	0.15 0.00	0.85 0.60	0.12	0.27 0.17	0.23 0.08	2.1 1.9	2.4 2.2	0.5	3.2 3.0	0.4	0.40 0.15	0.21 0.19	0.2	0.13	0.1	0.4 0.1	8° 0°

Notes

- Plastic or metal protrusions of 0.15 mm maximum per side are not included.
- 2. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	JEITA		PROJECTION '	ISSUE DATE
SOT765-1		MO-187				02-06-07

Fig 10. Package outline SOT765-1 (VSSOP8)

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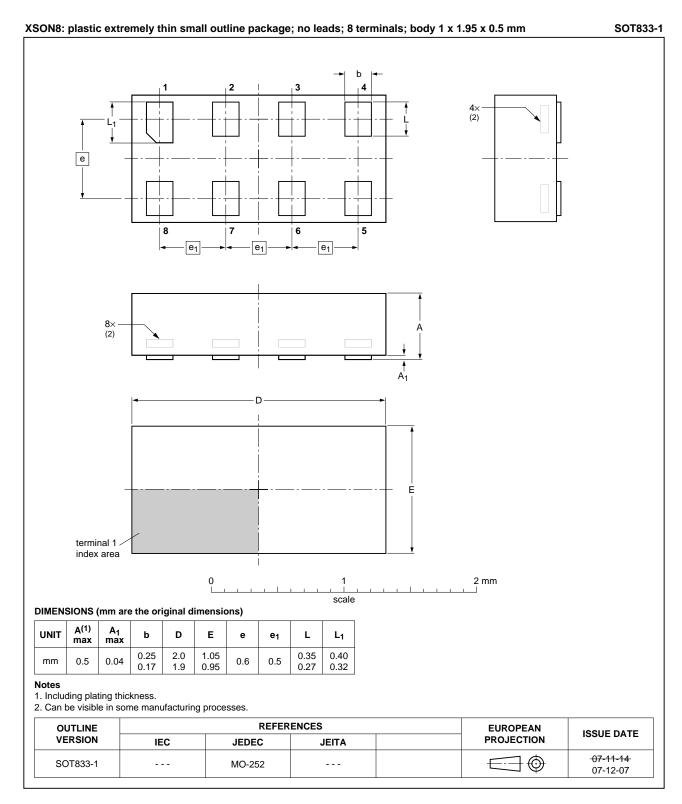


Fig 11. Package outline SOT833-1 (XSON8)

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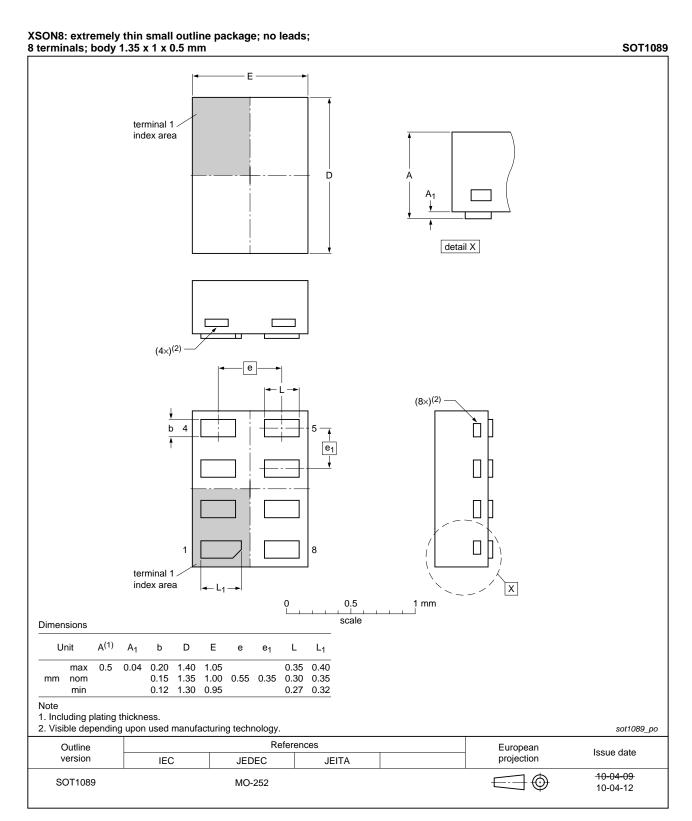


Fig 12. Package outline SOT1089 (XSON8)

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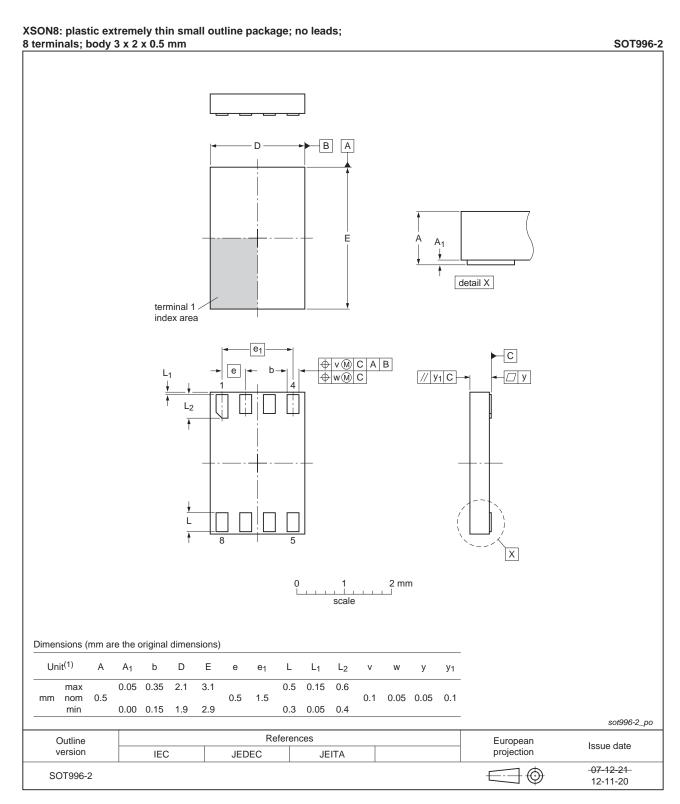


Fig 13. Package outline SOT996-2 (XSON8)

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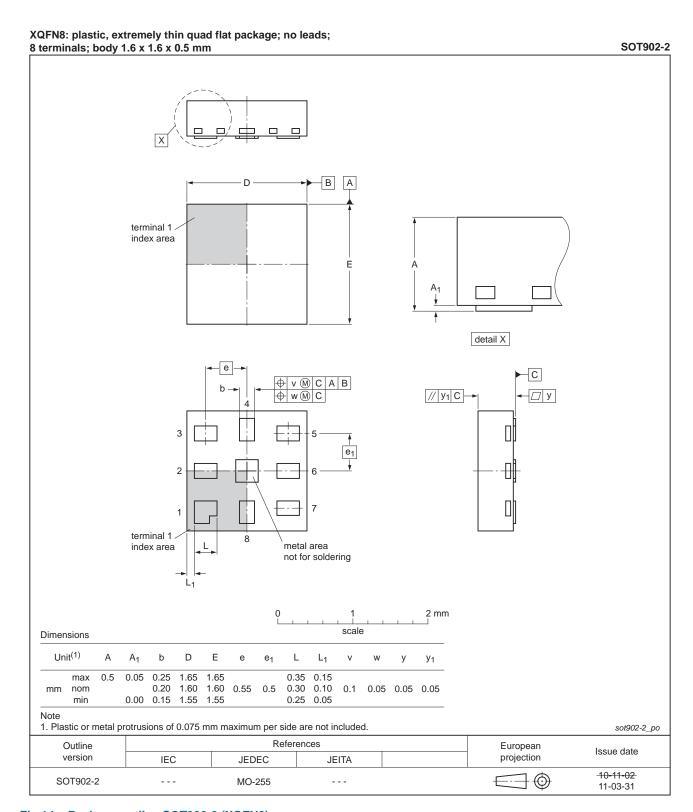


Fig 14. Package outline SOT902-2 (XQFN8)

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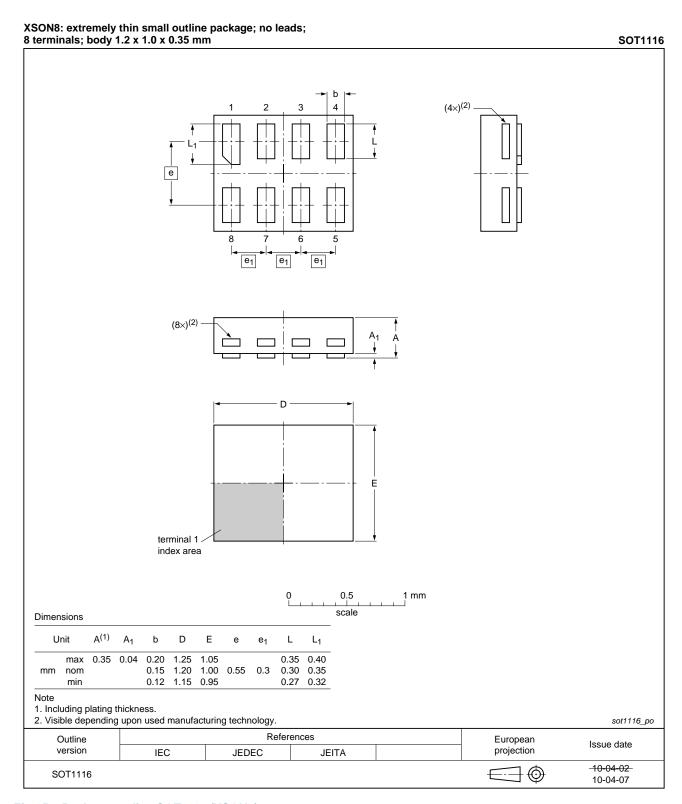


Fig 15. Package outline SOT1116 (XSON8)

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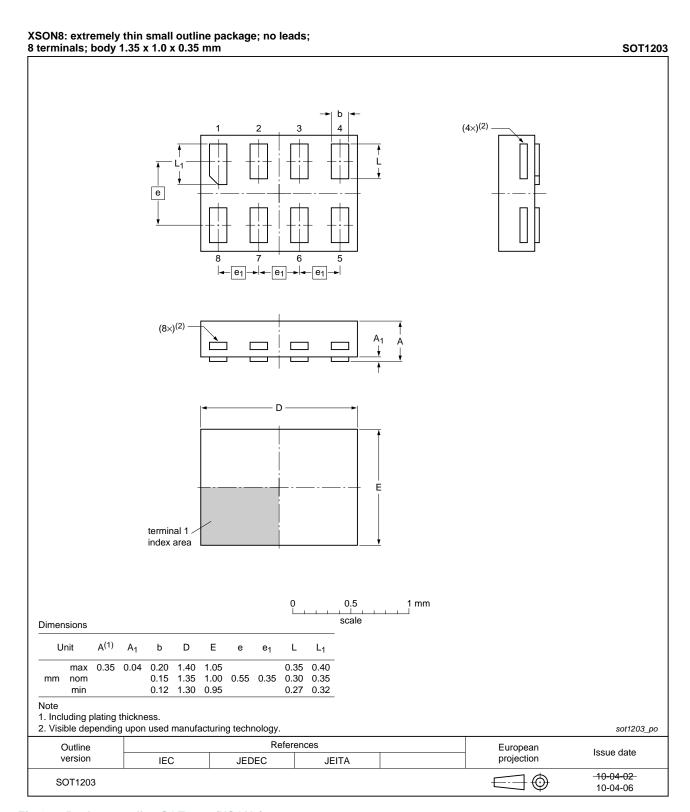


Fig 16. Package outline SOT1203 (XSON8)

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14. Abbreviations

Table 11. Abbreviations

Acronym	Description
CDM	Charged Device Model
DUT	Device Under Test
ESD	ElectroStatic Discharge
НВМ	Human Body Model
MM	Machine Model

15. Revision history

Table 12. Revision history

	•			
Document ID	Release date	Data sheet status	Change notice	Supersedes
74AUP2G38 v.8	20130211	Product data sheet	-	74AUP2G38 v.7
Modifications:	 For type num 	nber 74AUP2G38GD XSON8U	has changed to XS	ON8.
74AUP2G38 v.7	20120605	Product data sheet	-	74AUP2G38 v.6
74AUP2G38 v.6	20111209	Product data sheet	-	74AUP2G38 v.5
74AUP2G38 v.5	20100923	Product data sheet	-	74AUP2G38 v.4
74AUP2G38 v.4	20091008	Product data sheet	-	74AUP2G38 v.3
74AUP2G38 v.3	20090616	Product data sheet	-	74AUP2G38 v.2
74AUP2G38 v.2	20080312	Product data sheet	-	74AUP2G38 v.1
74AUP2G38 v.1	20061016	Product data sheet	-	-

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16. Legal information

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Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions"
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